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Exploring the optoelectronic properties of SnSe: A new insight

Manoj Kumar[1,2,3], Sanju Rani[1,2], Pargam Vashistha[1,4], Govind Gupta[1,4], Xu Wang[3*] and V.N. Singh[1,2*]

[1]Academy of Scientific and Innovative Research (AcSIR), Ghaziabad, Uttar Pradesh- 201002, India

[2]Indian Reference Materials (BND) Division, CSIR-National Physical Laboratory, Dr. K. S. Krishnan Marg, New Delhi-110012, India

[3]School of Engineering, RMIT University, VIC 3000 Australia

[4]Sensor Device Metrology Division, CSIR-National Physical Laboratory, Dr. K. S. Krishnan Marg, New Delhi 110012, India

Corresponding author: singhvn@nplindia.org (VNS) and xu.wang@rmit.edu.au (Xu Wang)

Supplementary Information-

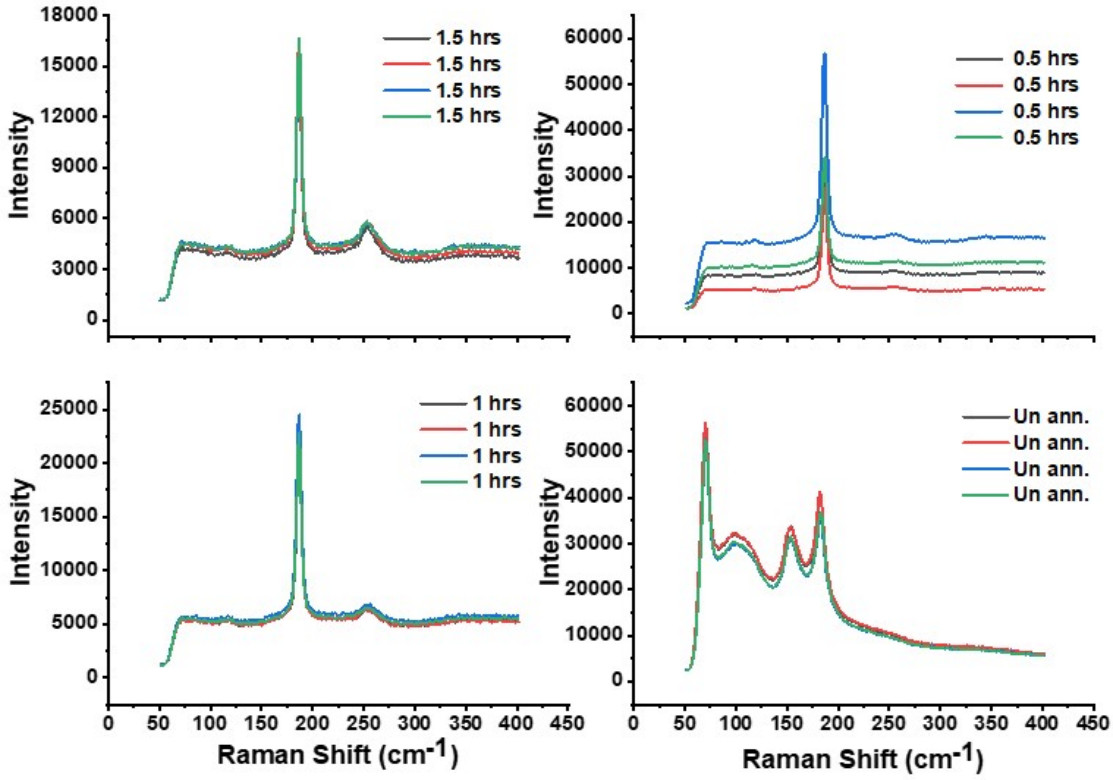

Figure S1 Raman spectra at randomly selected points on the film of the samples annealed at different times.

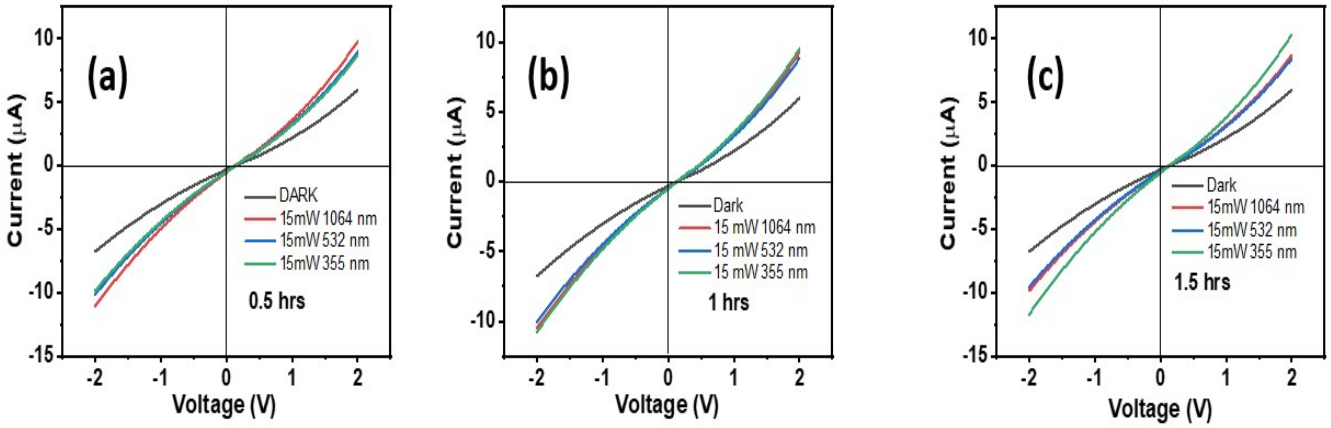

Figure S2. I-V of the devices under different conditions.

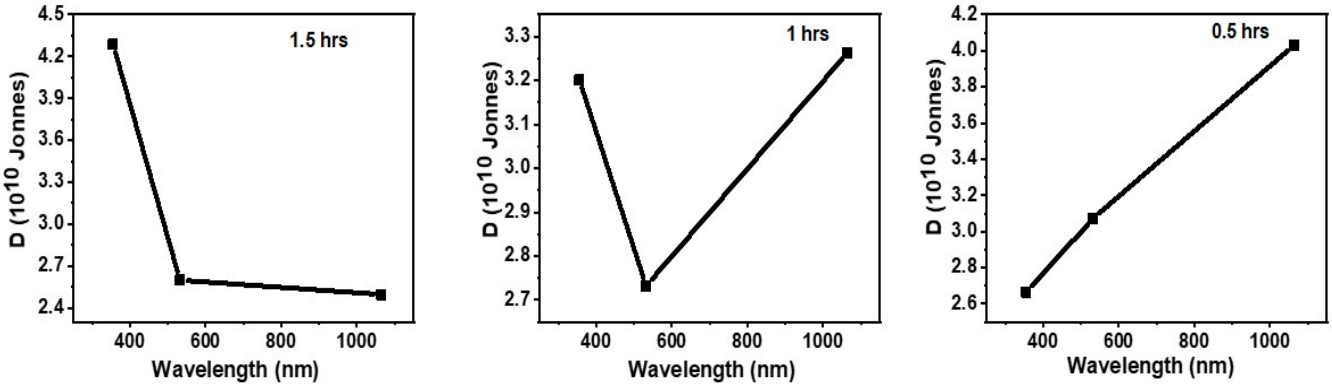

Figure S3. Detectivity of the devices

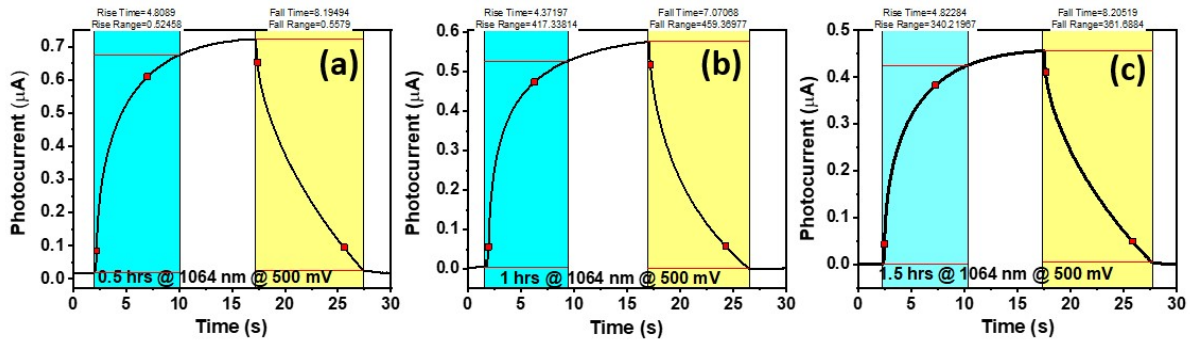

Figure S4. Rise and decay time fitting at 1064 nm of (a) 0.5, (b) 1, and (c) 1.5 hrs annealed devices.

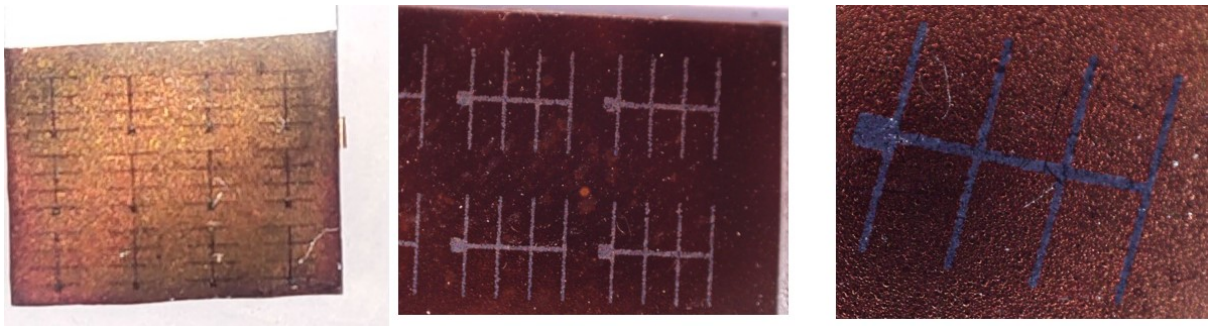

Figure S5. Images of an actual solar cell device of SnSe annealed at 300 ºC for one hour (having Ag silver contacts on the front face made using masking).

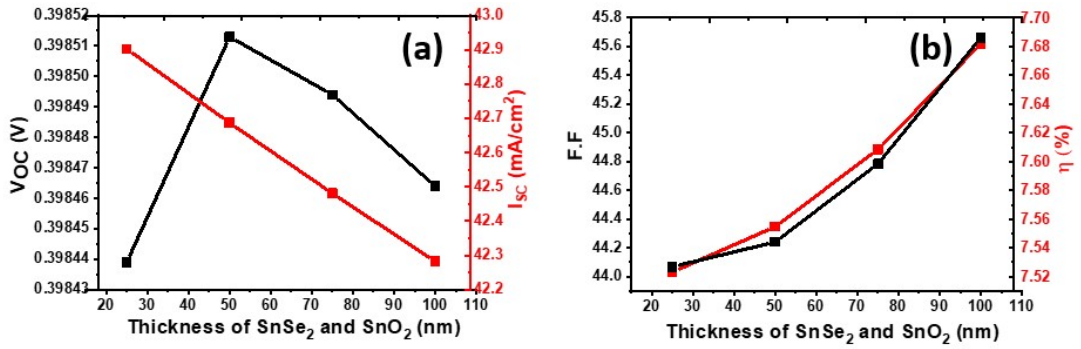

Figure S6. Effect of thickness of $SnSe_2$ and SnO_2 on the parameters, Voc, Jsc (a), FF, and efficiency (η) (b) of SnSe-based solar device.

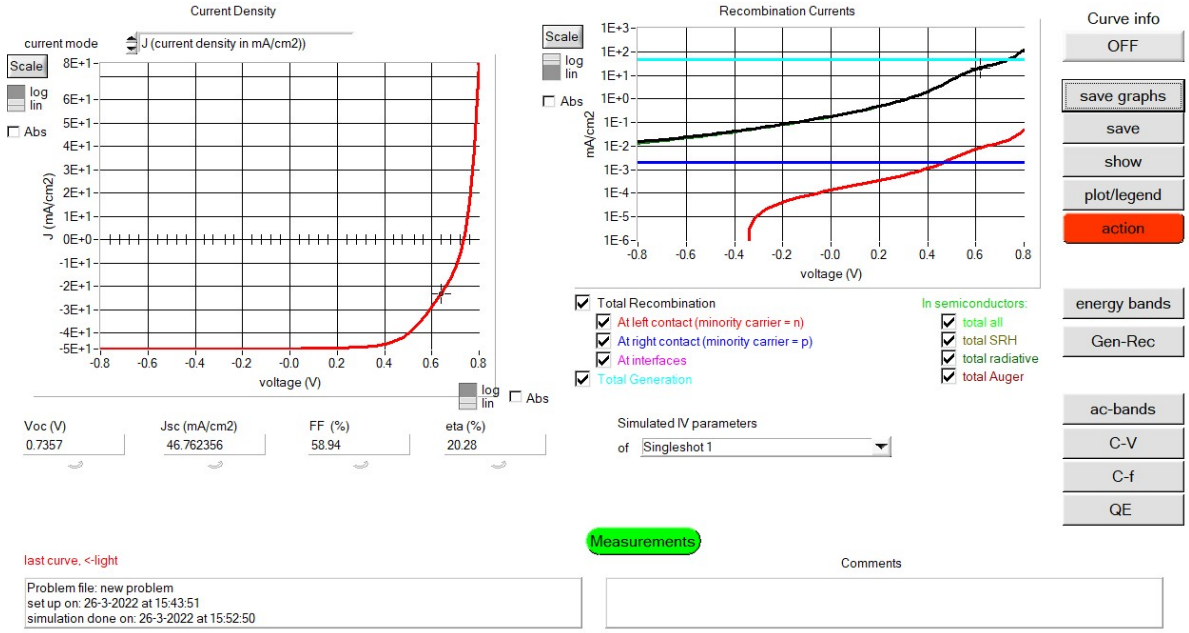

Figure S7. IV panel of the SCAPS-1D software shows efficiency of 20.28 %, with a back contact of 5.3 eV.